MMG100S120B6UC

1200V 100A IGBT Module

November 2018 Version 01 RoHS Compliant

PRODUCT FEATURES

☐ IGBT chip in trench FS-technology

☐ Low switching losses

☐ $V_{CE(sat)}$ with positive temperature coefficient

☐ Fast switching and short tail current

☐ Free wheeling diodes with fast and soft reverse recovery

APPLICATIONS

☐ Welding Machine

☐ Power Supplies

☐ Others

IGBT-inverter

ABSOLUTE MAXIMUM RATINGS(T_C =25°C unless otherwise specified)

Symbol	Parameter/Test Conditions		Values	Unit
V_{CES}	Collector Emitter Voltage	T_J=25℃	1200	V
V_{GES}	Gate Emitter Voltage		±20	
I_C	DC Collector Current	T_C=25℃,T_{Jmax}=175℃	145	A
		T_C=90℃,T_{Jmax}=175℃	100	
I_{CM}	Repetitive Peak Collector Current	tp=1ms	200	
P_{tot}	Power Dissipation Per IGBT	T_C=25℃,T_{Jmax}=175℃	555	W

Diode-inverter

ABSOLUTE MAXIMUM RATINGS (T_C =25°C unless otherwise specified)

Symbol	Parameter/Test Conditions		Values	Unit
V_{RRM}	Repetitive Reverse Voltage	T_J=25℃	1200	V
$I_{F(AV)}$	Average Forward Current		100	A
I_{FRM}	Repetitive Peak Forward Current	tp=1ms	200	
I^2t		T_J =125℃, t=10ms, V_R=0V	1150	A^2S

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IGBT-inverter

ELECTRICAL CHARACTERISTICS *(T_C=25°C unless otherwise specified)*

Symbol	Parameter/Test Conditions			Min.	Typ.	Max.	Unit
$V_{GE(th)}$	Gate Emitter Threshold Voltage	$V_{CE}=V_{GE}$, I_C=4mA		5.2	6.0	6.5	V
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	I_C=100A, V_{GE}=15V, T_J=25℃			2.2	2.65	
		I_C=100A, V_{GE}=15V, T_J=125℃			2.5		
		I_C=100A, V_{GE}=15V, T_J=150℃			2.6		
I_{CES}	Collector Leakage Current	V_{CE}=1200V, V_{GE}=0V, T_J=25℃				100	μA
		V_{CE}=1200V, V_{GE}=0V, T_J=150℃				1	mA
I_{GES}	Gate Leakage Current	V_{CE}=0V,V_{GE}=±20V, T_J=25℃		-400		400	nA
R_{gint}	Integrated Gate Resistor				5		Ω
Q_g	Gate Charge	V_{CE}=600V, I_C=100A , V_{GE}=15V			0.48		μC
C_{ies}	Input Capacitance	V_{CE}=25V, V_{GE}=0V, f =1MHz			7.8		nF
C_{res}	Reverse Transfer Capacitance				300		pF
$t_{d(on)}$	Turn on Delay Time	V_{CC}=600V,I_C=100A R_G =5.1Ω, V_{GE}=±15V, Inductive Load	T_J=25℃		150		ns
			T_J=125℃		160		ns
			T_J=150℃		170		ns
t_r	Rise Time		T_J=25℃		45		ns
			T_J=125℃		50		ns
			T_J=150℃		50		ns
$t_{d(off)}$	Turn off Delay Time	V_{CC}=600V,I_C=100A R_G =5.1Ω, V_{GE}=±15V, Inductive Load	T_J=25℃		330		ns
			T_J=125℃		380		ns
			T_J=150℃		400		ns
t_f	Fall Time		T_J=25℃		70		ns
			T_J=125℃		80		ns
			T_J=150℃		90		ns
E_{on}	Turn on Energy	V_{CC}=600V,I_C=100A R_G =5.1Ω, V_{GE}=±15V, Inductive Load	T_J=125℃		14.5		mJ
			T_J=150℃		15.5		mJ
E_{off}	Turn off Energy		T_J=125℃		5		mJ
			T_J=150℃		5.5		mJ
I_{SC}	Short Circuit Current	tpsc≤10μS , V_{GE}=15V T_J=150℃,V_{CC}=600V			510		A
R_{thJC}	Junction to Case Thermal Resistance （Per IGBT）					0.27	K /W

Diode-inverter

ELECTRICAL CHARACTERISTICS *(T_C=25°C unless otherwise specified)*

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit
V_F	Forward Voltage	I_F=100A , V_{GE}=0V, T_J=25℃		1.8	2.3	V
		I_F=100A , V_{GE}=0V, T_J=125℃		1.9		
		I_F=100A , V_{GE}=0V, T_J=150℃		1.9		
t_{rr}	Reverse Recovery Time	I_F=100A , V_R=600V dI_F/dt=-2500A/μs T_J =150℃		400		ns
I_{RRM}	Max. Reverse Recovery Current			115		A
Q_{RR}	Reverse Recovery Charge			23		μC
E_{rec}	Reverse Recovery Energy			8.7		mJ
R_{thJCD}	Junction to Case Thermal Resistance （Per Diode）				0.6	K /W

MODULE CHARACTERISTICS *(T_C=25°C unless otherwise specified)*

Symbol	Parameter/Test Conditions		Values	Unit
T_{Jmax}	Max. Junction Temperature		175	℃
T_{Jop}	Operating Temperature		-40~150	
T_{stg}	Storage Temperature		-40~125	
V_{isol}	Isolation Breakdown Voltage	AC, 50Hz(R.M.S), t=1minute	3000	V
CTI	Comparative Tracking Index		＞200	
Torque	to heatsink	Recommended（M6）	3~5	Nm
	to terminal	Recommended（M5）	2.5~5	Nm
Weight			160	g

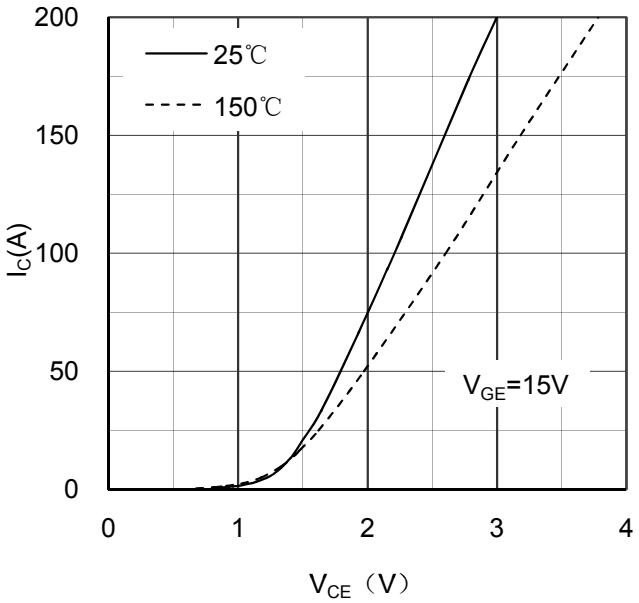


Figure 1. Typical Output Characteristics IGBT-inverter

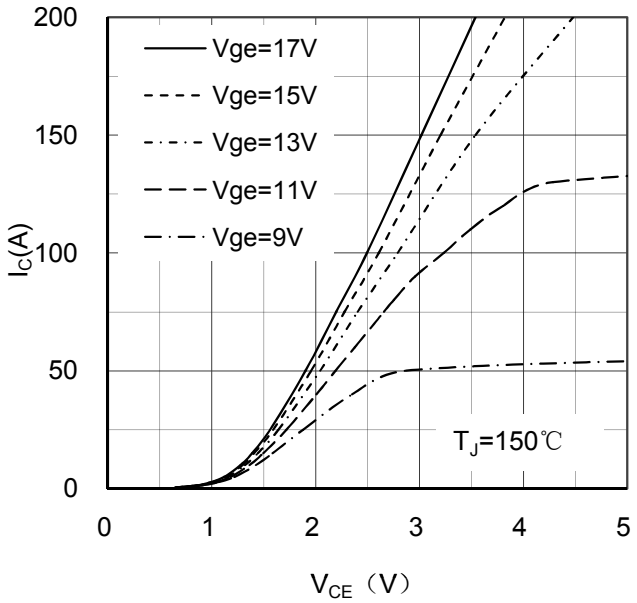


Figure 2. Typical Output Characteristics IGBT-inverter

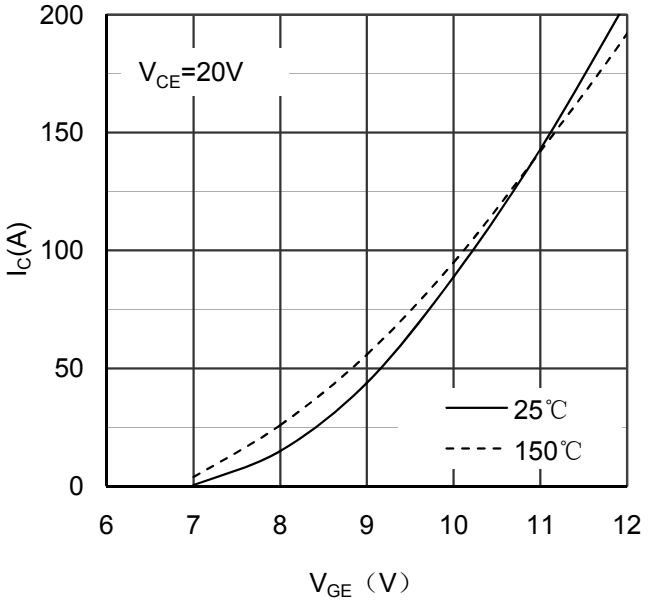


Figure 3. Typical Transfer characteristics IGBT-inverter

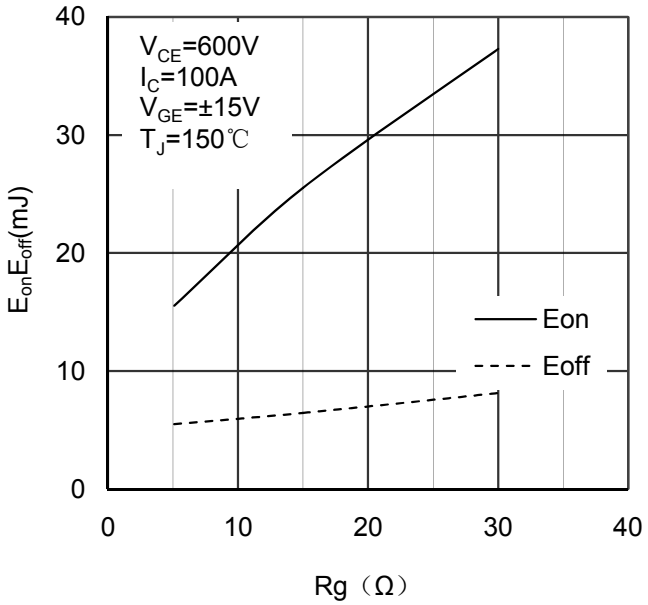


Figure 4. Switching Energy vs Gate Resistor IGBT-inverter

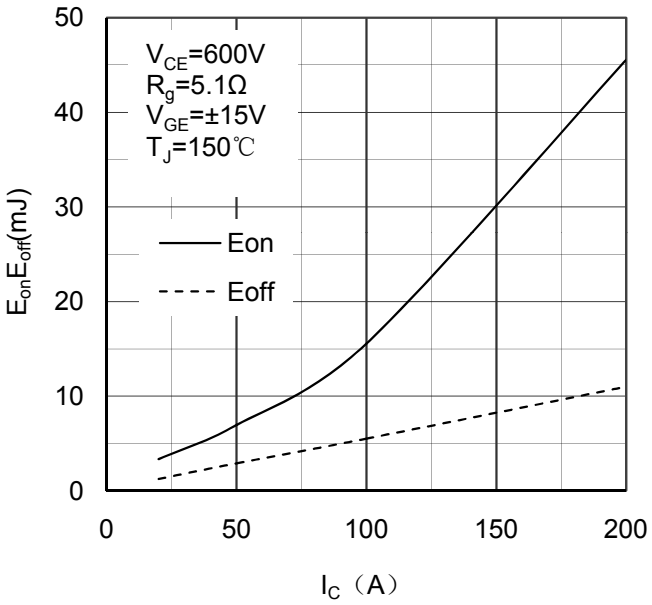


Figure 5. Switching Energy vs Collector Current IGBT-inverter

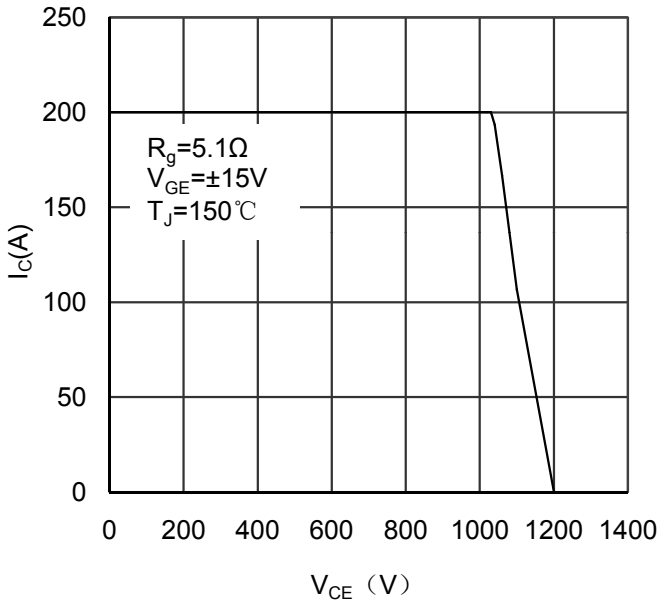


Figure 6. Reverse Biased Safe Operating Area IGBT-inverter

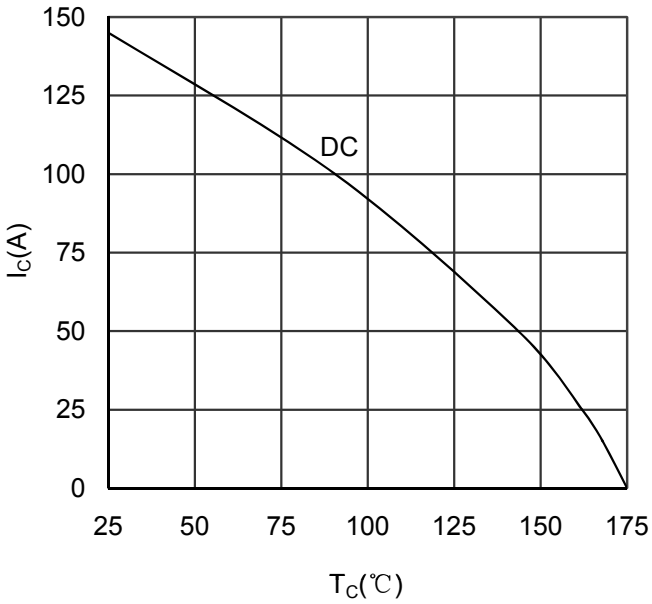


Figure 7. Collector Current vs Case temperature IGBT -inverter

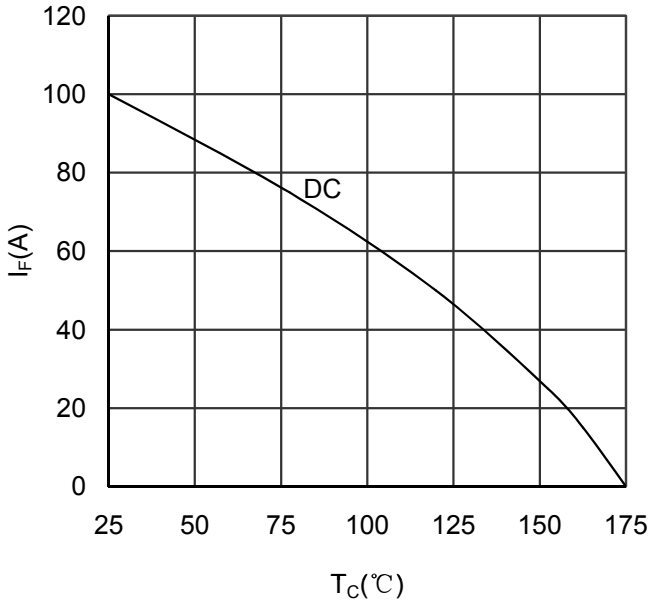


Figure 8. Forward current vs Case temperature Diode -inverter

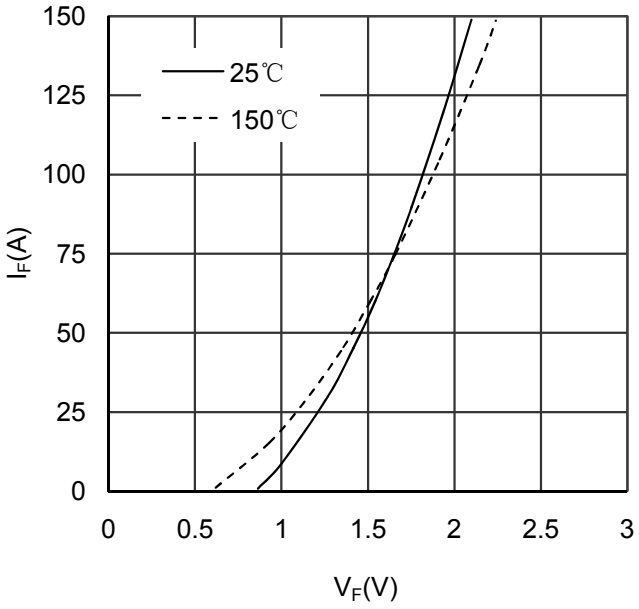


Figure 9. Diode Forward Characteristics Diode -inverter

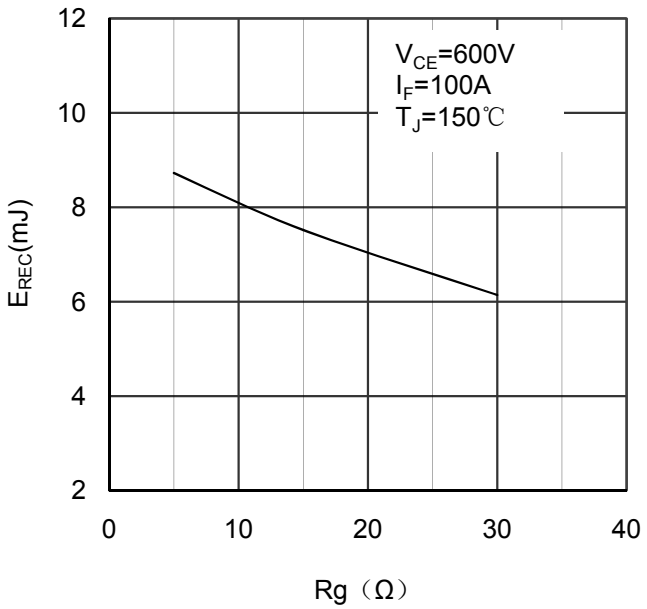


Figure 10. Switching Energy vs Gate Resistor Diode -inverter

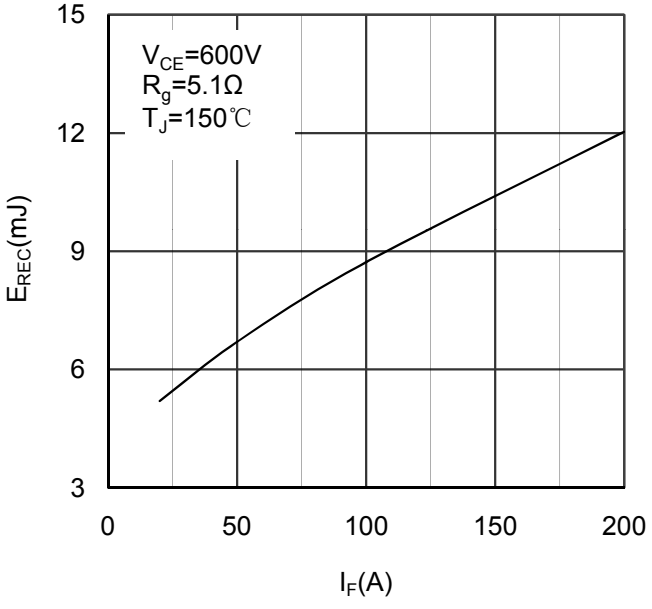


Figure 11. Switching Energy vs Forward Current Diode-inverter

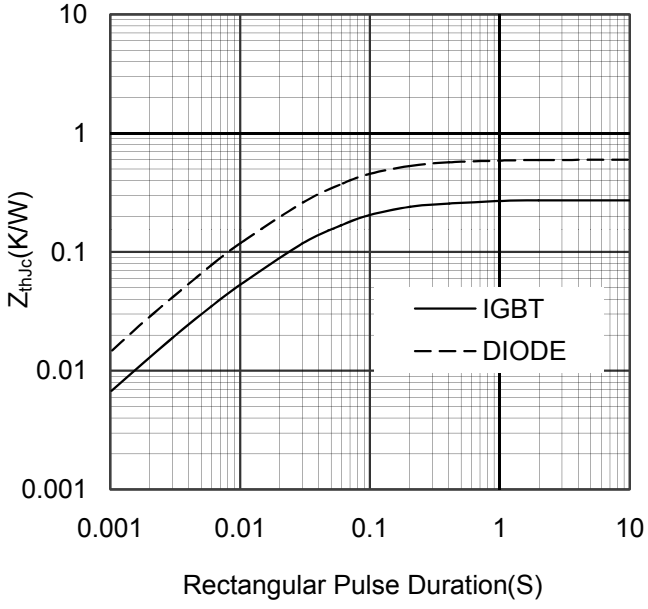


Figure 12. Transient Thermal Impedance of Diode and IGBT-inverter

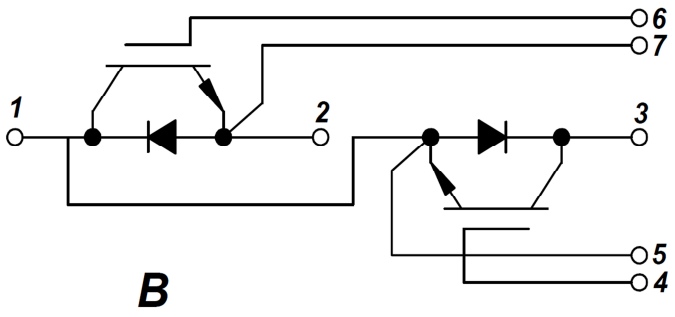
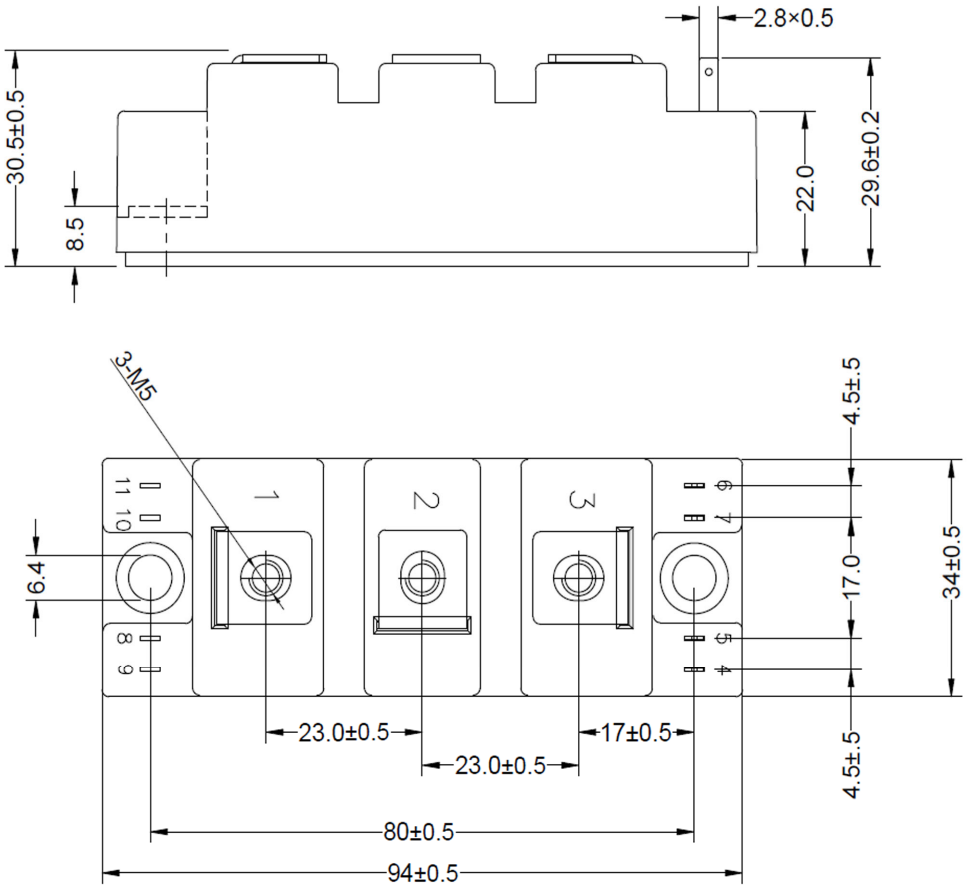


Figure 13. Circuit Diagram



Dimensions in (mm)

Figure 14. Package Outline